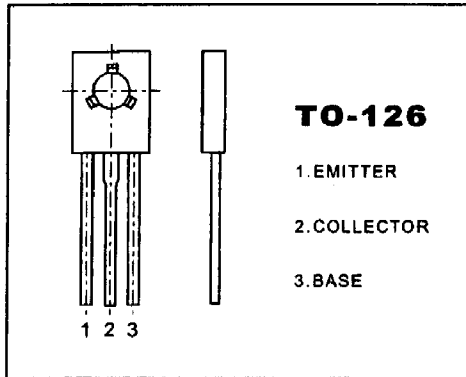


BD233/235/237 TRANSISTOR(NPN)



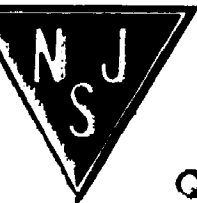
FEATURES

- Power dissipation**
 P_{CM} : 1.25 W ($T_{amb}=25^{\circ}C$)
- Collector current**
 I_{CM} : 2 A
- Collector-base voltage**
 $V_{(BR)CBO}$: BD233 : 45V
 BD235 : 60V
 BD237: 100V
- Operating and storage junction temperature range**
 T_{stg} : $-65^{\circ}C$ to $+150^{\circ}C$
 T_J : $150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	BD233	BD235	BD237	Units
Collector-base breakdown voltage	45	60	100	V
	$V_{(BR)CBO}$		$I_C = 100 \mu A, I_E = 0$	
Collector-emitter breakdown voltage	45	60	80	V
	$V_{(BR)CEO}$		$I_C = 10 mA, I_B = 0$	
Emitter-base breakdown voltage	$V_{(BR)EBO}$		5	V
Collector cut-off current	100	100	100	μA
	I_{CBO}		$V_{CE} = 45 V, I_E = 0$	
			$V_{CE} = 60 V, I_E = 0$	
Emitter cut-off current	I_{EBO}		1	mA
			$V_{EB} = 5 V, I_C = 0$	
DC current gain	40	25		
	$h_{FE(1)}$		$V_{CE} = 2 V, I_C = 150 mA$	
Collector-emitter saturation voltage	$V_{CE(sat)}$		0.6	V
			$I_C = 1 A, I_B = 100 mA$	
Transition frequency	f_T		3	MHz
				$f = 10 MHz$



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